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74	SR Tietjen et al., "Vapor Phase Growth Technique and Sys Compound Semiconductors," Electronic Research Cer										D				<u> </u>
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- 1	UR	Azoulay et al., "MOCVD n-Type Doping of GaAs and GaAlAs Using Silicon and Selenium and Fabrication of Double Heterstructure Bipolar Transistor," Journal of Crystal Growth, 68 (1984) pp. 453-460.													
	VR	Hiramatsu et al.					MOVP	E Growth	og Gal	l Film on		x	_	+	+
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	WR	Khan et al., "Effect of Si on Photoluminescence of GaN," Solid State													
	\	Communications, Vol. 57, No. 6, 1986, pp. 405-409. Bass, "Silicon and Germanium Doping of Epitaxial Gallium Arsenide Grown by the												+	+
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